

ABSTRACT

An infrared sensor includes a series capacitor element and a reference capacitor element each exhibiting a predetermined capacitance value; an infrared-detecting capacitor element whose capacitance value varies depending on an intensity of infrared light incident on the element; and an output node being a node at which a first terminal of the series capacitor element, a first terminal of the reference capacitor element and a first terminal of the infrared-detecting capacitor element are connected to one another. A potential of the output node is brought to a reference potential by applying a predetermined voltage between a second terminal of the series capacitor element and a second terminal of the reference capacitor element; a potential of the output node is brought to a detection potential by applying the predetermined voltage between the second terminal of the series capacitor element and a second terminal of the infrared-detecting capacitor element; and the intensity of infrared light is output as a potential difference between the reference potential and the detection potential.